SELECTED ITEM DRAWING

			ANALOG DEVICES	
Unless otherwise specified DIMENSIONS ARE IN INCHES (MM)	TOLERANCES: .XX +/- 0.010 .XXX +/- 0.005 .XXXX +/- 0.002 ANGLES +/- .5 DEG	Drawing practices per **ASME Y14.100**	**18 GHz to 29 GHz Output, x2 Active Frequency Multiplier**	
			SIZE **A**	DRAWING NUMBER **SID000060**

SID000060 **Rev. A**

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1. SCOPE

1.1. Scope

This drawing establishes the requirements for the 18 GHz to 29 GHz Output, GaAs, PHEMT, MMIC, x2 Active Frequency Multiplier, to be screened in accordance with MIL-PRF-38534, Class K, to the requirements specified in 4.1, and 4.2 herein.

1.2. Analog Devices Part Number

Generic Part Number	Screened Part Number
ADH576S	HMC8332

2. APPLICABLE DOCUMENTS

2.1. Government Documents

Unless otherwise specified, the following drawings and standards, of the issue in effect on the date of the accepted purchase order, in the Department of Defense Index of Specifications and Standards (DODISS) and supplement thereto, shall form a part of this drawing to the extent specified herein.

DEPARTMENT OF DEFENSE TEST METHOD STANDARD

MIL-STD-883 Microcircuits

DEPARTMENT OF DEFENSE PERFORMANCE SPECIFICATIONS

MIL-PRF-38534 Hybrid Microcircuits, General Specifications For

2.2. Non-Government Documents

The following documents, of the issue in effect on the date of the purchase order, form a part of this drawing to the extent specified herein:

Analog Devices Inc.

HMC576-Die Data Sheet	Commercial Product Die Datasheet	v00.0506 (Reference Only)

3. REQUIREMENTS

3.1. General Requirements
The devices delivered shall comply to this specification.

3.2. Design Construction and Physical Dimensions
The design construction and physical dimensions shall be as defined in Figure 1 herein.

3.3. Traceability
Each delivered device shall be traceable to the wafer number and the wafer lot number of each device. Inspection lot records shall be maintained to provide traceability to the specific wafer and wafer lot from which the chips originated.

3.4. Burn-In and Life Test Circuit
The burn-in and life test circuit and conditions shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test methods 1005 and 1015 per MIL-STD-883.

4. QUALITY ASSURANCE PROVISIONS

4.1. Wafer Acceptance Testing
The wafer lot acceptance testing shall consist of Class Level S inspections per MIL-STD-883 TM 5007. All deliverable Die shall have passed 100% element electrical test per 4.2.1. Element evaluation per 4.2.2 and passed 100% visual inspection, per MIL-STD-883 TM2010 Condition A, after wafer dicing.

4.2. Dice Qualification Requirements
Dice qualification requirements shall be in accordance with MIL-PRF-38534, Appendix C, Table C-II, per Class K.

4.2.1. Element Electrical Test (RF-On Wafer)
Electrical tests shall consist of the tests specified on Table I, tested at room temperature only.

4.2.2. Element Evaluation (Lot Acceptance Testing)
Sample Die shall be randomly selected from the wafer that has successfully passed RF-On wafer testing per 4.2.1 and shall be mounted to suitable fixturing for screening.

4.2.2.1. Initial Electrical Test (Pre Burn-In)
Pre Burn-In electrical tests shall consist of the tests specified on Table II, tested at room temperature only.

4.2.2.2. Interim Electrical Test (Post Burn-In)
Post Burn-In electrical tests shall consist of the tests specified on Table II, tested at room temperature only and shall meet performance requirements in accordance with Table II and Table III.

4.2.2.3. Final Electrical Test (Post Life Test)
Final electrical tests shall consist of the tests specified in Table II, tested at -40 °C and +85 °C, which shall be Read and Record only, and shall meet performance requirements in accordance with Table II and Table III.

5. MIL-PRF-38534 EXCEPTIONS

5.1. Wafer Fabrication

Foundry information is available upon request.

5.2. Microcircuit Dice Evaluation Requirements (TABLE C-II)

- Pre-screen test post assembly required to Die qualification to remove all assembly related rejects.
- Subgroup 4: mechanical shock or constant acceleration not performed.
- Subgroup 4: Interim and post burn-in electrical tests will include tests screened at +25 °C only.

6. PREPARATION FOR DELIVERY

The preparation for delivery, packaging, preservation, ESD protection and handling shall be in accordance with MIL-PRF-38534.

6.1. Die Packaging Information

The Die shall be delivered in accordance with Table IV herein.

6.2. Inspection Data Requirements

The following data shall accompany each shipment.

a. A Certificate of Conformance (C of C) certifies that the lot(s) meets all requirements of this specification.
b. Die Photograph
c. Attribute data for all tests.
d. Wafer Lot Acceptance data including photos from SEM inspection in 4.1.
e. Summary of RF-On wafer test data per 4.2.1.
f. Element Evaluation test results per 4.2.2.
    a. Variables data for electrical end-point measurements.
g. Failure Analysis with photos (If applicable)
h. A cover sheet indicating the following purchasing information:
    1. Customer purchase order number.
    2. Analog Devices part number.
    3. Part lot identification codes.
    4. Date & quantity shipped.

TABLE I: DIE ELECTRICAL CHARACTERISTICS

Parameter	Conditions 1/ Unless otherwise specified	Limits		Units
		Min	Max	
Output Power	F_{IN} = 9 GHz, 12 GHz, and 14 GHz	11		dBm
Supply Current (Idd1)	No Signal at RFIN		68	mA
Supply Current (Idd2)			40	mA

TABLE I Note:
1/ Limits apply at +25 °C only with Vdd1 = Vdd2 = +5 V and Drive Level = + 3 dBm

TABLE II: ELECTRICAL CHARACTERISTICS FOR QUALIFICATION SAMPLES

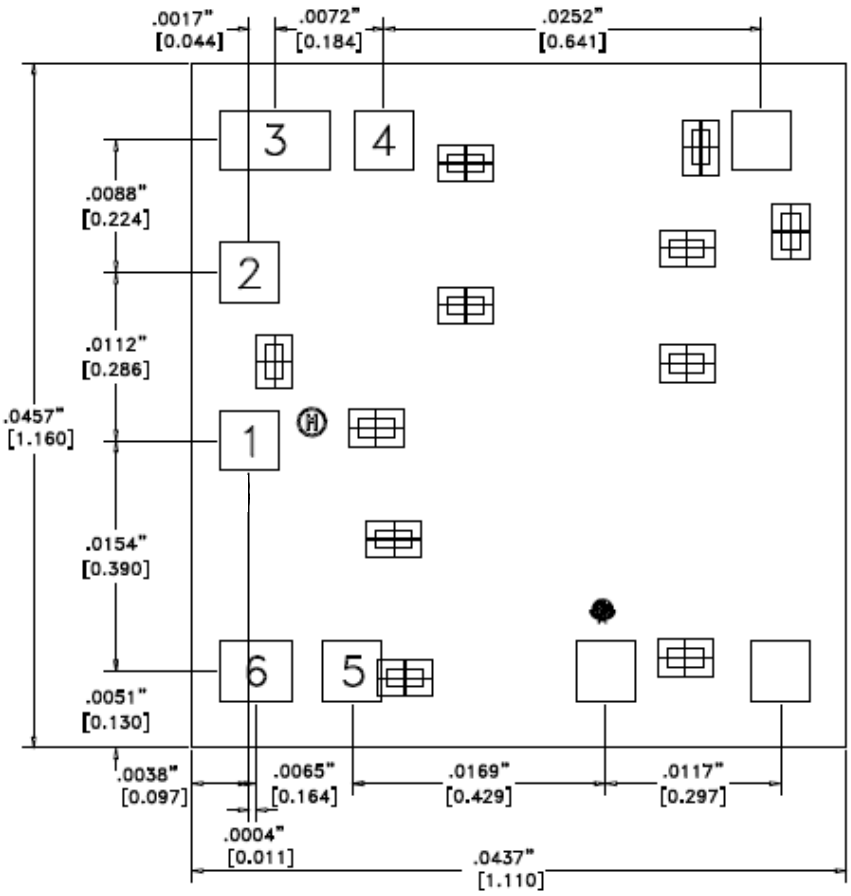
Parameter	Conditions 1/2/3/ Unless otherwise specified	Sub-Group	Limits		Units
			Min	Max	
Output Power	F_{IN} = 9 GHz, 12 GHz, and 14 GHz	4	11		dBm
Supply Current (Idd1 + Idd2)	No Signal at RFIN	1		108	mA

TABLE II Notes:
1/ Limits apply at +25 °C with Vdd1 = Vdd2 = +5 V and Drive Level = +3 dBm.
3/ -40 °C and +85 °C (Subgroup 2, 3, 5 and 6) shall be Read and Record only.
3/ See MIL-PRF-38534 Table C-Xa for subgroup parameter definitions.

TABLE III: BURN-IN/LIFE TEST DELTA LIMITS 1/2/3/

Parameter	Test Conditions	Delta Limits	Units
Output Power	Per Table II	± 1	dB
Supply Current (Idd1 +Idd2)		± 10	%

TABLE III Notes:
1/ Delta test is performed at T_A = +25 °C only.
2/ Table II limits will not be exceeded.
3/ Delta calculated pre/post 240 hours and post 240 hours / post 1000 hours.



NOTES:

1. ALL DIMENSIONS ARE IN INCHES [MM]
2. DIE THICKNESS IS .004"
3. BOND PAD METALIZATION: GOLD
4. BACKSIDE METALIZATION: GOLD
5. BACKSIDE METAL IS GROUND
6. OVERALL DIE SIZE ±.002"

PAD	DESCRIPTION	PAD SIZE
1	Vdd1	.0039[.100] X .0039[.100]
2	Vdd2	.0039[.100] X .0039[.100]
3	RFOUT	.0074[.188] X .0039[.100]
4, 5	GND	.0039[.100] X .0039[.100]
6	RFIN	.0048[.121] X .0039[.100]

Figure 1 – Device Outline for the HMC8332

TABLE IV: DIE PACKAGING INFORMATION

Standard Package	Alternate
GP-2 (Gel Pack)	1/

TABLE IV Note:
1/ For alternate packaging information, contact Analog Devices Inc.

ORDERING GUIDE

Model	Temperature Range
HMC8332	–40 °C to +85 °C

Revision History

Revision History		
Rev	**Description of Change**	**Date**
A	Initial release.	01/15/2025